

状态	型号	容量	NAND工艺	尺寸(mm)	封装球数	Performance(MB/s) Seq ReadSeq Write	供电电压	接口电压	待机功耗电流(NA)	sleep mode电流 (NAND)	支持平台	备注
UFS2.0	KLUC261CF-P00B1	16GB	11nm MLC	11.5±1.3±1.0	153	440	2.0 3.3V	1.8Vr 3.3V	130mA	0uA (1n auto power saving mode 50uA #25指		64Gb x 2
UFS2.0	KLUC2401CF-P00B1	32GB	11nm MLC	11.5±1.3±1.0	153	460	1.8Vr 3.3V	1.8Vr 3.3V	230mA	0uA (1n auto power saving mode 70uA #25指		64Gb x 2
UFS2.0	KLUC2411CF-P00B1	64GB	11nm MLC	11.5±1.3±1.0	153	460	1.8Vr 3.3V	1.8Vr 3.3V	230mA	0uA (1n auto power saving mode 70uA #25指		128Gb x 4
UFS2.0	KLUC2811CF-P00B1	128GB	11nm MLC	11.5±1.3±1.2	153	460	1.8Vr 3.3V	1.8Vr 3.3V	230mA	0uA (1n auto power saving mode 130uA #25指		128Gb x 8
UFS2.0	KLUC2811CF-C00B1	128GB	11nm MLC	11.5±1.3±1.04	153	460	1.8Vr 3.3V	1.8Vr 3.3V	230mA	0uA (1n auto power saving mode 130uA #25指		128Gb x 8
UFS2.0	KLUC2811CF-P00B1	256GB	48 layer	11.5±1.3±1.2	153	850	2.0 3.3V	1.8Vr 3.3V	450mA	0uA (1n auto power saving mode 130uA #25指		256Gb x 8
UFS2.1	KLUC2411EF-P00C1	64GB	11nm MLC	11.5±1.3±1.0	153	880	2.0 3.3V	1.8Vr 3.3V	370mA	0uA (1n auto power saving mode 450uA #25指		128Gb x 4
UFS2.1	KLUC2811EF-P00C1	128GB	48 layer	11.5±1.3±1.0	153	880	2.0 3.3V	1.8Vr 3.3V	370mA	0uA (1n auto power saving mode 450uA #25指		128Gb x 8
UFS2.1	KLUC2811EF-P00C1	256GB	48 layer	11.5±1.3±1.0	153	880	2.0 3.3V	1.8Vr 3.3V	370mA	0uA (1n auto power saving mode 450uA #25指		256Gb x 8
UFS2.1	KLUC2811EA-P00C1	64GB	64 layer	11.5±1.3±1.0	153	910	2.0 3.3V	1.8Vr 3.3V	390mA	0uA (1n auto power saving mode 40uA #25指		256Gb MLC x 2
UFS2.1	KLUC4011EA-P00C1	128GB	64 layer	11.5±1.3±1.0	153	950	2.0 3.3V	1.8Vr 3.3V	390mA	0uA (1n auto power saving mode 70uA #25指		256Gb TLC x 4
UFS2.1	KLUC8011EA-P00C1	256GB	64 layer	11.5±1.3±1.0	153	950	2.0 3.3V	1.8Vr 3.3V	390mA	0uA (1n auto power saving mode 130uA #25指		256Gb TLC x 8
UFS2.1	KLUC8011EF-P00C1	512GB	64 layer	11.5±1.3±1.0	153	910	2.0 3.3V	1.8Vr 3.3V	390mA	0uA (1n auto power saving mode 130uA #25指		256Gb TLC x 8
UFS3.0	KLUC40HDE-B2D1	128GB	V6 92 layer	11.5±1.3±0.8	153	1800	2.0 3.3V	1.2Vr 2.5/3.3V	400mA	0uA (1n auto power saving mode 180uA #25指		256Gb TLC x 4
UFS3.0	KLUC80HDE-B2D1	256GB	V6 92 layer	11.5±1.3±0.8	153	2000	4.0 3.3V	1.2Vr 2.5/3.3V	400mA	0uA (1n auto power saving mode 180uA #25指		256Gb TLC x 8
UFS3.0	KLUC80HDE-C2D1	256GB	V6 92 layer	11.5±1.3±1.0	153	2000	4.0 3.3V	1.2Vr 2.5/3.3V	400mA	0uA (1n auto power saving mode 180uA #25指		256Gb TLC x 8
UFS3.0	KLUC80HDE-B2D1	512GB	V6 92 layer	11.5±1.3±1.0	153	2000	4.0 3.3V	1.2Vr 2.5/3.3V	400mA	0uA (1n auto power saving mode 180uA #25指		512Gb TLC x 8
UFS3.0	KLUC40HDE-B2E1	128GB	V6 92 layer	11.5±1.3±0.8	153	1800	2.0 3.3V	1.2Vr 2.5/3.3V	400mA	0uA (1n auto power saving mode 180uA #25指		256Gb TLC x 4
UFS3.1	KLUC80HDE-C2E1	256GB	V6 92 layer	11.5±1.3±1.0	153	2000	4.0 3.3V	1.2Vr 2.5/3.3V	400mA	0uA (1n auto power saving mode 180uA #25指		256Gb TLC x 8
UFS3.1	KLUC80HDE-B2E1	512GB	V6 92 layer	11.5±1.3±1.0	153	2000	4.0 3.3V	1.2Vr 2.5/3.3V	400mA	0uA (1n auto power saving mode 180uA #25指		512Gb TLC x 8